

IN THE CLAIMS:

Please add new claim 84 as follows:

--84. A method of manufacturing a semiconductor device comprising the steps of:
 forming a silicon nitride film containing at least one of hydrogen and oxygen over a substrate;
 depositing a semiconductor film comprising amorphous silicon on said silicon nitride film;
 disposing a metal in contact with at least a selected portion of said semiconductor film;
and
 heating said semiconductor film and said metal to crystallize said semiconductor film.--

REMARKS

At the outset, the Examiner is thanked for the thorough review and consideration of the present application.

With respect to new claim 84, Applicants respectfully submit that it is generic to all other designated species.